



CSD23203WT Information



For Reference Only

Part Number CSD23203WT
Manufacturer Texas Instruments

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 8V 3A 6DSBGA

Package 6-UFBGA, DSBGA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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CSD23203WT Specifications

Manufacturer Part NumberCSD23203WTManufacturerTexas InstrumentsCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackage6-UFBGA, DSBGASeriesNexFET?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)8VCurrent - Continuous Drain (Id) @ 25°C3A (Ta)Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id1.1V @ 250μAGate Charge (Qg) (Max) @ Vgs6.3nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds914pF @ 4VVgs (Max)-6VFET Feature-Power Dissipation (Max)750mW (Ta)Rds On (Max) @ Id, Vgs19.4 mOhm @ 1.5A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)		
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Series NexFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 8V Current - Continuous Drain (Id) @ 25°C 3A (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1.1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 6.3nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 914pF @ 4V Vgs (Max) -6V FET Feature - Power Dissipation (Max) 750mW (Ta) Rds On (Max) @ Id, Vgs 19.4 mOhm @ 1.5A, 4.5V		Transistors - FETs, MOSFETs - Single
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)8VCurrent - Continuous Drain (Id) @ 25°C3A (Ta)Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id1.1V @ 250μAGate Charge (Qg) (Max) @ Vgs6.3nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds914pF @ 4VVgs (Max)-6VFET Feature-Power Dissipation (Max)750mW (Ta)Rds On (Max) @ Id, Vgs19.4 mOhm @ 1.5A, 4.5V	Series	NexFET?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 3A (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1.1V @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 8V 3A (Ta) 1.8V, 4.5V 4.5V 4.5V 4.5V 6.3nC @ 4.5V 914pF @ 4V -6V FET Feature - Power Dissipation (Max) 750mW (Ta) 19.4 mOhm @ 1.5A, 4.5V	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1.1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 6.3nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 914pF @ 4V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3A (Ta) 1.8V, 4.5V - 4.5V - 3A (Ta) 3A (Ta) - 4 3A (Ta) - 3A (Ta) - 3A (Ta) - 4 3A (Ta) - 4 3A (Ta)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1.1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 6.3nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 914pF @ 4V Vgs (Max) -6V FET Feature - Power Dissipation (Max) 750mW (Ta) Rds On (Max) @ Id, Vgs 19.4 mOhm @ 1.5A, 4.5V	Drain to Source Voltage (Vdss)	8V
Vgs(th) (Max) @ Id 1.1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 6.3nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 914pF @ 4V Vgs (Max) -6V FET Feature - Power Dissipation (Max) 750mW (Ta) Rds On (Max) @ Id, Vgs 19.4 mOhm @ 1.5A, 4.5V	Current - Continuous Drain (Id) @ 25°C	3A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6.3nC @ 4.5V 914pF @ 4V -6V -750mW (Ta) 19.4 mOhm @ 1.5A, 4.5V	Drive Voltage (Max Rds On, Min Rds On)	1.8V, 4.5V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 914pF @ 4V -6V -6V -750mW (Ta) 19.4 mOhm @ 1.5A, 4.5V	Vgs(th) (Max) @ Id	1.1V @ 250μA
Vgs (Max) -6V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 19.4 mOhm @ 1.5A, 4.5V	Gate Charge (Qg) (Max) @ Vgs	6.3nC @ 4.5V
FET Feature - Power Dissipation (Max) 750mW (Ta) Rds On (Max) @ Id, Vgs 19.4 mOhm @ 1.5A, 4.5V	Input Capacitance (Ciss) (Max) @ Vds	914pF @ 4V
Power Dissipation (Max) 750mW (Ta) Rds On (Max) @ Id, Vgs 19.4 mOhm @ 1.5A, 4.5V	Vgs (Max)	-6V
Rds On (Max) @ Id, Vgs 19.4 mOhm @ 1.5A, 4.5V	FET Feature	-
	Power Dissipation (Max)	750mW (Ta)
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	Rds On (Max) @ Id, Vgs	19.4 mOhm @ 1.5A, 4.5V
F	Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type Surface Mount	Mounting Type	Surface Mount
Supplier Device Package 6-DSBGA	Supplier Device Package	6-DSBGA
Package / Case 6-UFBGA, DSBGA	Package / Case	6-UFBGA, DSBGA
Report errors?		Report errors?

CSD23203WT Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

CSD23203WT Payment Methods





















CSD23203WT Shipping Methods













If you have any question about CSD23203WT, please do not hesitate to contact us!

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